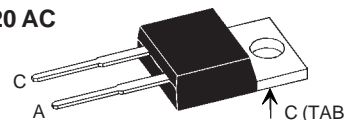
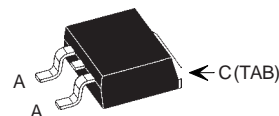


# HiPerFRED™ Epitaxial Diode with soft recovery

**$I_{FAV} = 30\text{ A}$**   
 **$V_{RRM} = 600\text{ V}$**   
 **$t_{rr} = 30/35\text{ ns}$**

$V_{RSM}$ V	$V_{RRM}$ V	Type
600	600	DSEP 29-06A
600	600	DSEP 29-06AS
600	600	DSEP 29-06B


**TO-220 AC**

**TO-263**


A = Anode, C = Cathode, TAB = Cathode

Symbol	Conditions	Maximum Ratings	
$I_{FRMS}$		35	A
$I_{FAVM}$	rect., d = 0.5; $T_C$ (Version A, AS) = 135°C $T_C$ (Version B) = 125°C	30 30	A A
$I_{FSM}$	$T_{VJ} = 45^\circ\text{C}$ ; $t_p = 10\text{ ms}$ (50 Hz), sine; (Version A, AS) (Version B)	250 200	A A
$E_{AS}$	$T_{VJ} = 25^\circ\text{C}$ ; non-repetitive $I_{AS} = 1.3\text{ A}$ ; $L = 180\ \mu\text{H}$	0.2	mJ
$I_{AR}$	$V_A = 1.5 \cdot V_R$ typ.; $f = 10\text{ kHz}$ ; repetitive	0.1	A
$T_{VJ}$		-55...+175	°C
$T_{VJM}$		175	°C
$T_{stg}$		-55...+150	°C
$P_{tot}$	$T_C = 25^\circ\text{C}$	165	W
$M_d$	mounting torque (Version A, B)	0.4...0.6	Nm
Weight	typical	2	g

## Features

- International standard package
- Planar passivated chips
- Very short recovery time
- Extremely low switching losses
- Low  $I_{RM}$ -values
- Soft recovery behaviour
- Epoxy meets UL 94V-0

## Applications

- Antiparallel diode for high frequency switching devices
- Antisaturation diode
- Snubber diode
- Free wheeling diode in converters and motor control circuits
- Rectifiers in switch mode power supplies (SMPS)
- Inductive heating
- Uninterruptible power supplies (UPS)
- Ultrasonic cleaners and welders

Symbol	Conditions	Characteristic max. Values		
		Version A	Version B	
$I_R$ ①	$T_{VJ} = 25^\circ\text{C}$ ; $V_R = V_{RRM}$ $T_{VJ} = 150^\circ\text{C}$ ; $V_R = V_{RRM}$	250 1	250 2	$\mu\text{A}$ mA
$V_F$ ②	$I_F = 30\text{ A}$ ; $T_{VJ} = 150^\circ\text{C}$ $T_{VJ} = 25^\circ\text{C}$	1.26 1.61	1.58 2.52	V V
$R_{thJC}$		0.9	0.9	K/W
$R_{thCH}$	typ.	0.5	0.5	K/W
$t_{rr}$ typ.	$I_F = 1\text{ A}$ ; $-di/dt = 200\text{ A}/\mu\text{s}$ ; $V_R = 30\text{ V}$ ; $T_{VJ} = 25^\circ\text{C}$	35	30	ns
$I_{RM}$ typ.	$V_R = 100\text{ V}$ ; $I_F = 50\text{ A}$ ; $-di_F/dt = 100\text{ A}/\mu\text{s}$ $T_{VJ} = 100^\circ\text{C}$	6	4	A

## Advantages

- Avalanche voltage rated for reliable operation
- Soft reverse recovery for low EMI/RFI
- Low  $I_{RM}$  reduces:
  - Power dissipation within the diode
  - Turn-on loss in the commutating switch

Pulse test: ① Pulse Width = 5 ms, Duty Cycle < 2.0 %  
 ② Pulse Width = 300  $\mu\text{s}$ , Duty Cycle < 2.0 %

Data according to IEC 60747 and per diode unless otherwise specified

IXYS reserves the right to change limits, test conditions and dimensions.

Dimensions see pages D4 - 85-86

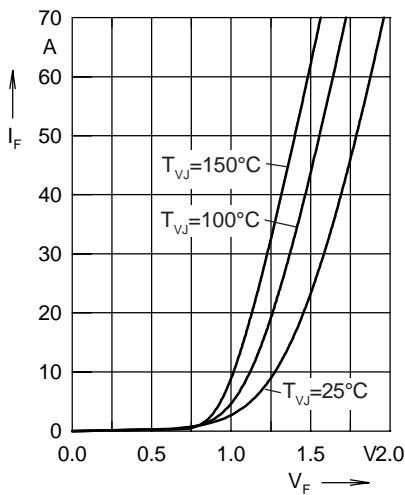


Fig. 1 Forward current  $I_F$  versus  $V_F$

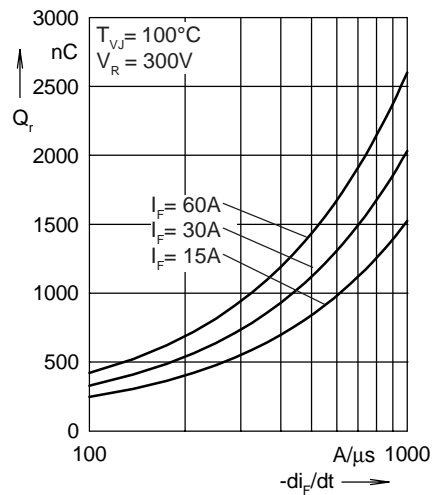


Fig. 2 Reverse recovery charge  $Q_r$  versus  $-di_F/dt$

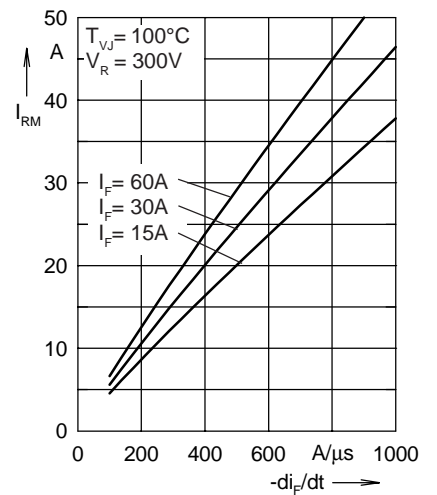


Fig. 3 Peak reverse current  $I_{RM}$  versus  $-di_F/dt$

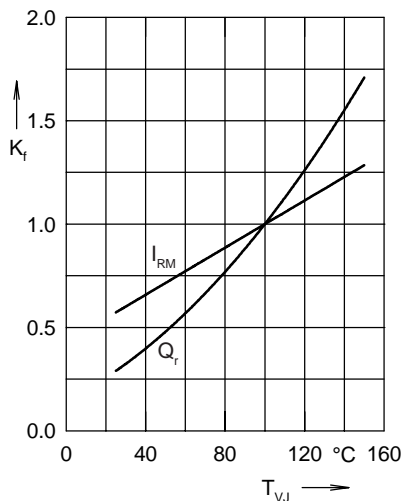


Fig. 4 Dynamic parameters  $Q_r$ ,  $I_{RM}$  versus  $T_{VJ}$

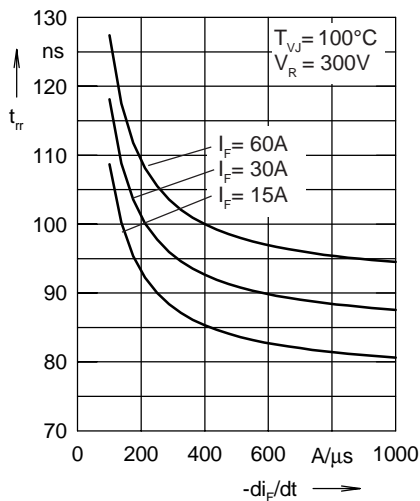


Fig. 5 Recovery time  $t_{rr}$  versus  $-di_F/dt$

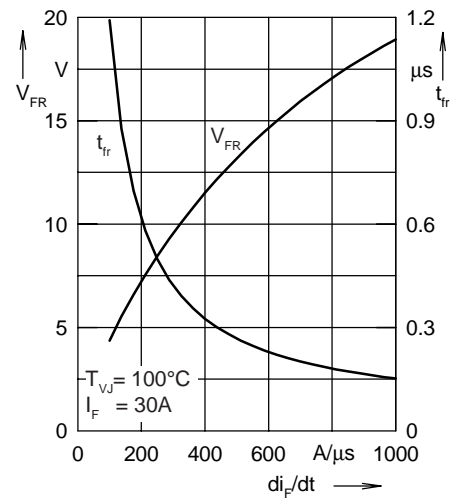


Fig. 6 Peak forward voltage  $V_{FR}$  and  $t_{fr}$  versus  $di_F/dt$

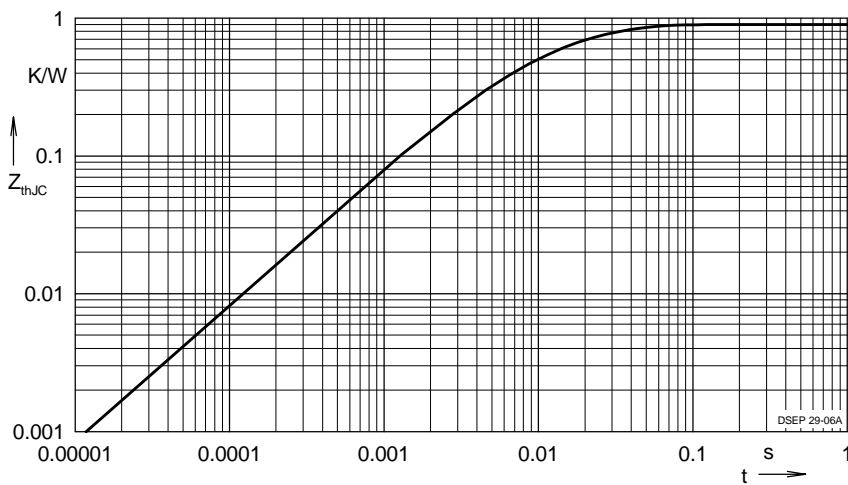


Fig. 7 Transient thermal resistance junction to case

Constants for  $Z_{thJC}$  calculation:

i	$R_{thi}$ (K/W)	$t_i$ (s)
1	0.502	0.0052
2	0.193	0.0003
3	0.205	0.0162

NOTE: Fig. 2 to Fig. 6 shows typical values

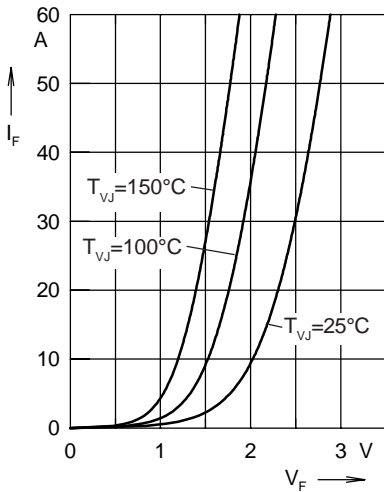


Fig. 1 Forward current  $I_F$  versus  $V_F$

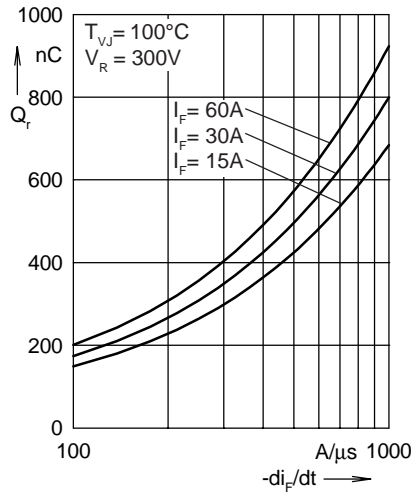


Fig. 2 Reverse recovery charge  $Q_r$  versus  $-di_F/dt$

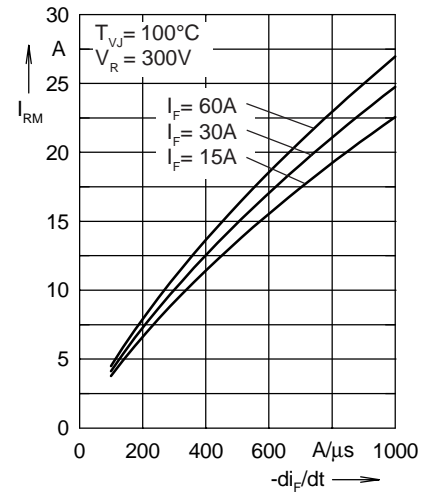


Fig. 3 Peak reverse current  $I_{RM}$  versus  $-di_F/dt$

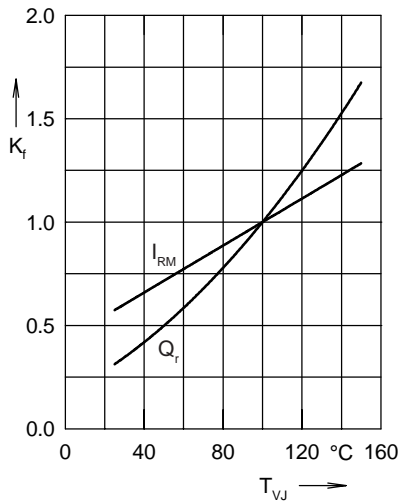


Fig. 4 Dynamic parameters  $Q_r$ ,  $I_{RM}$  versus  $T_{VJ}$

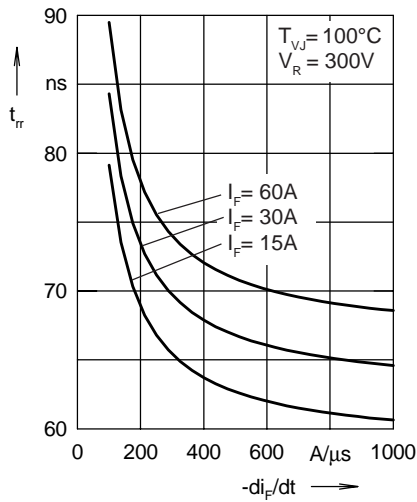


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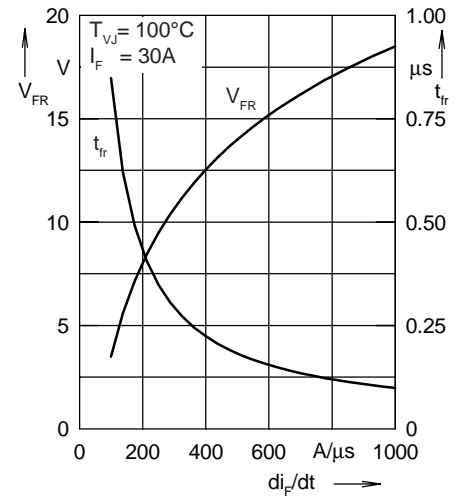


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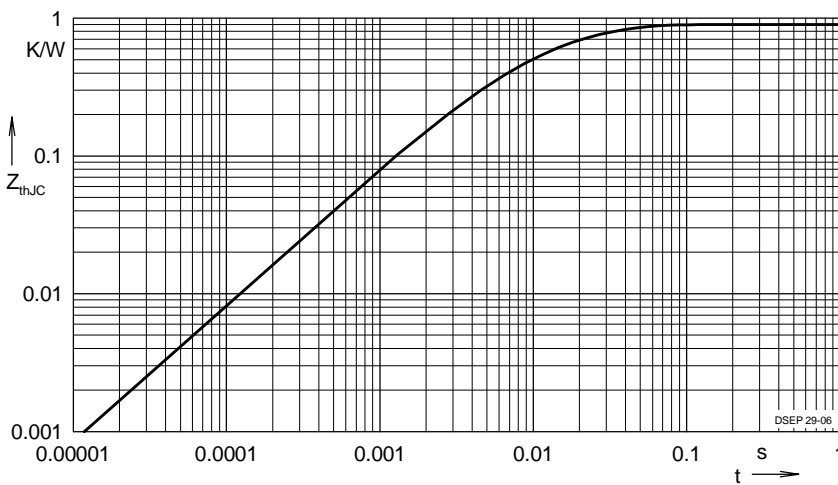


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